PH2729-8.5M

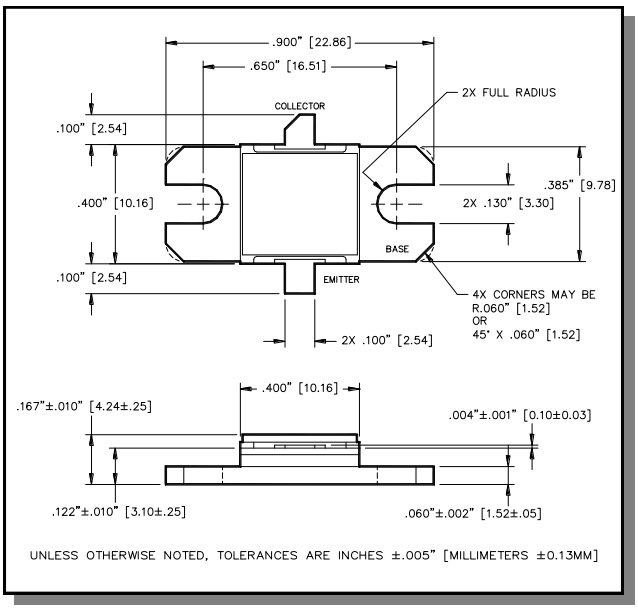
Radar Pulsed Power Transistor
8.5W, 2.7-2.9 GHz, 100µs Pulse, 10% Duty

Rev. V1

Features

- NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS compliant

Outline Drawing



Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	65	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	I_C	1.8	A
Power Dissipation @ +25°C	P_{TOT}	65	W
Storage Temperature	T_{STG}	-65 to +200	°C
Junction Temperature	T_J	200	°C

Electrical Specifications: T_C = 25 ± 5°C (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	I_C = 10mA		BV_{CES}	65	-	V
Collector-Emitter Leakage Current	V_{CE} = 40V		I_{CES}	-	1.5	mA
Thermal Resistance	Vcc = 36V, Pin = 1.3W	F = 2.7, 2.8, 2.9 GHz	$R_{TH(JC)}$	-	2.2	°C/W
Output Power	Vcc = 36V, Pin = 1.3W	F = 2.7, 2.8, 2.9 GHz	P_{OUT}	8.5	-	W
Power Gain	Vcc = 36V, Pin = 1.3W	F = 2.7, 2.8, 2.9 GHz	G_P	8.15	-	dB
Collector Efficiency	Vcc = 36V, Pin = 1.3W	F = 2.7, 2.8, 2.9 GHz	η_C	35	-	%
Pulse Droop	Vcc = 36V, Pin = 1.3W	F = 2.7, 2.8, 2.9 GHz	Droop	-	0.7	dB
Input Return Loss	Vcc = 36V, Pin = 1.3W	F = 2.7, 2.8, 2.9 GHz	RL	-	-6	dB
Load Mismatch Tolerance	Vcc = 36V, Pin = 1.3W	F = 2.7, 2.8, 2.9 GHz	VSWR-T	-	3:1	-
Load Mismatch Stability	Vcc = 36V, Pin = 1.3W	F = 2.7, 2.8, 2.9 GHz	VSWR-S	-	1.5:1	-

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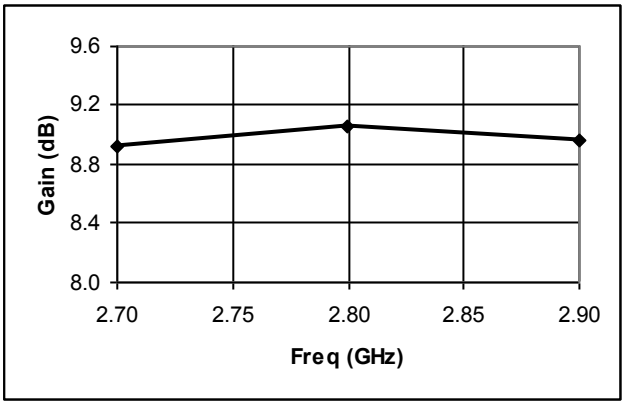
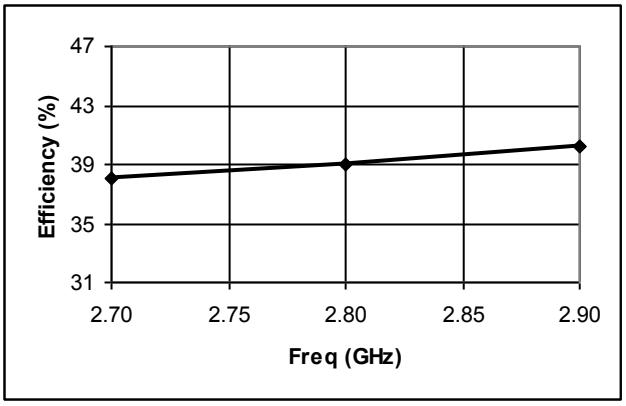
Typical RF Performance

Freq. (GHz)	Pin (W)	Pout (W)	Gain (dB)	Ic (A)	Eff (%)	RL (dB)	Droop (dB)	VSWR-S (1.5:1)	VSWR-T (3:1)
2.7	1.3	10.2	8.92	0.74	38.0	-18.1	0.11	S	P
2.8	1.3	10.5	9.06	0.75	39.1	-16.7	0.14	S	P
2.9	1.3	10.3	8.97	0.71	40.3	-12.5	0.21	S	P

Gain vs. Frequency

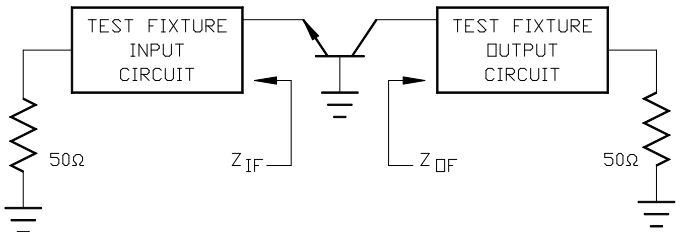


Collector Efficiency vs. Frequency



RF Test Fixture Impedance

F (GHz)	Z_{IF} (Ω)	Z_{OF} (Ω)
2.7	40 - j12	25 + j3.5
2.8	38 - j14	20 + j2.0
2.9	35 - j16	16 + j2.4



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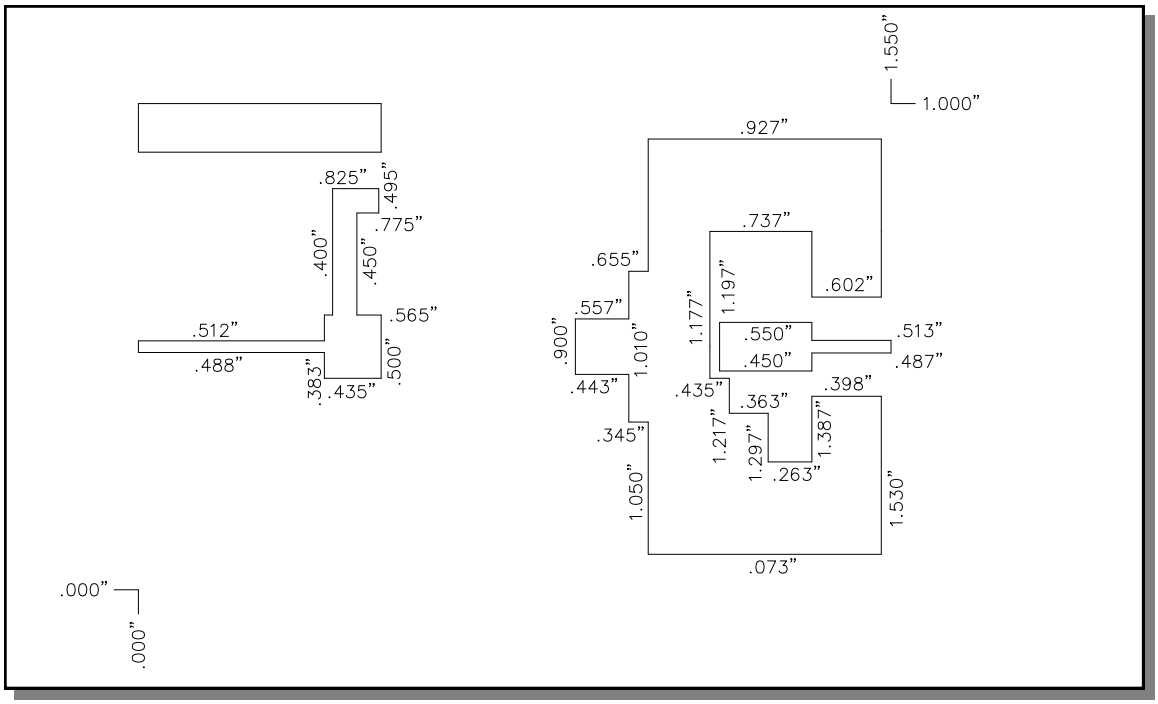
Test Fixture Circuit Dimensions



Test Fixture Assembly